

CR05AS-8

Thyristor

Low Power Use

REJ03G0543-0100

Rev.1.00

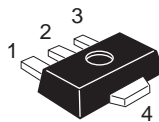
Mar.01.2005

Features

- $I_{T(AV)}$: 0.5 A
- V_{DRM} : 400 V
- I_{GT} : 100 μ A
- Non-Insulated Type
- Planar Passivation Type

Outline

PLZZ0004CA-A
(Package name: UPAK)



1. Cathode
2. Anode
3. Gate
4. Anode

Applications

Solid state relay, strobe flasher, igniter, and hybrid IC

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		8 (Mark CD)	
Repetitive peak reverse voltage	V_{RRM}	400	V
Non-repetitive peak reverse voltage	V_{RSM}	500	V
DC reverse voltage	$V_{R(DC)}$	320	V
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	400	V
DC off-state voltage ^{Note1}	$V_{D(DC)}$	320	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I_T (RMS)	0.79	A	
Average on-state current	I_T (AV)	0.5	A	Commercial frequency, sine half wave 180° conduction, $T_a = 57^\circ\text{C}$ ^{Note2}
Surge on-state current	I_{TSM}	10	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	0.4	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	0.1	W	
Average gate power dissipation	P_G (AV)	0.01	W	
Peak gate forward voltage	V_{FGM}	6	V	
Peak gate reverse voltage	V_{RGM}	6	V	
Peak gate forward current	I_{FGM}	0.1	A	
Junction temperature	T_j	- 40 to +125	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +125	$^\circ\text{C}$	
Mass	—	50	mg	Typical value

Notes: 1. With gate to cathode resistance $R_{GK} = 1\text{ k}\Omega$.

Electrical Characteristics

Parameter	Symbol	Rated value			Unit	Test conditions
		Min.	Typ.	Max.		
Repetitive peak reverse current	I_{RRM}	—	—	0.1	mA	$T_j = 125^\circ\text{C}$, V_{RRM} applied
Repetitive peak off-state current	I_{DRM}	—	—	0.1	mA	$T_j = 125^\circ\text{C}$, V_{DRM} applied, $R_{GK} = 1\text{ k}\Omega$
On-state voltage	V_{TM}	—	—	1.9	V	$T_a = 25^\circ\text{C}$, $I_{TM} = 1.5\text{ A}$, instantaneous value
Gate trigger voltage	V_{GT}	—	—	0.8	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 0.1\text{ A}$ ^{Note4}
Gate non-trigger voltage	V_{GD}	0.2	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$, $R_{GK} = 1\text{ k}\Omega$
Gate trigger current	I_{GT}	20	—	100 ^{Note3}	μA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 0.1\text{ A}$ ^{Note4}
Holding current	I_H	—	—	3	mA	$T_j = 25^\circ\text{C}$, $V_D = 12\text{ V}$, $R_{GK} = 1\text{ k}\Omega$
Thermal resistance	$R_{th(j-a)}$	—	—	70	$^\circ\text{C/W}$	Junction to ambient ^{Note2}

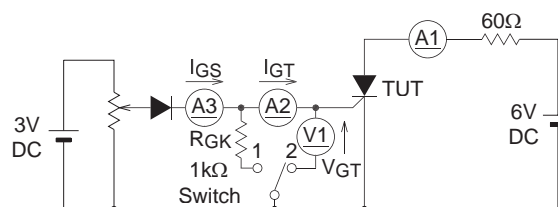
Notes: 2. Soldering with ceramic plate (25 mm × 25 mm × 0.7 mm).

3. If special values of I_{GT} are required, choose item E from those listed in the table below if possible.

Item	B	E
I_{GT} (μA)	20 to 50	20 to 100

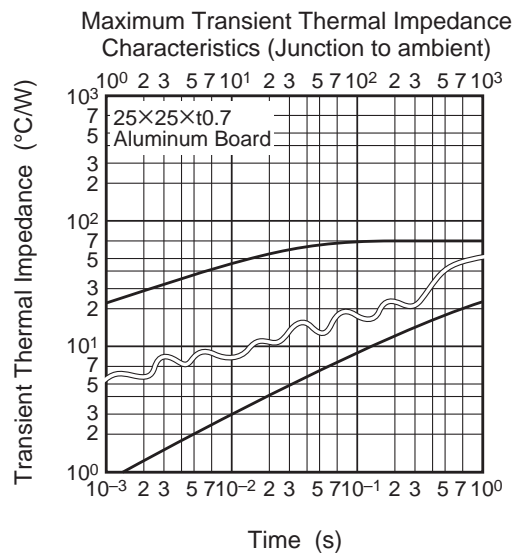
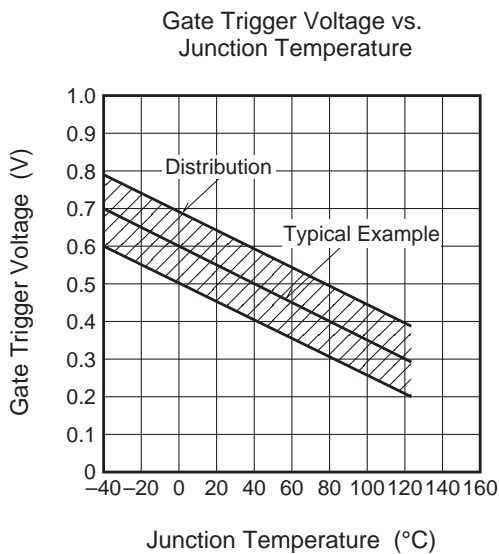
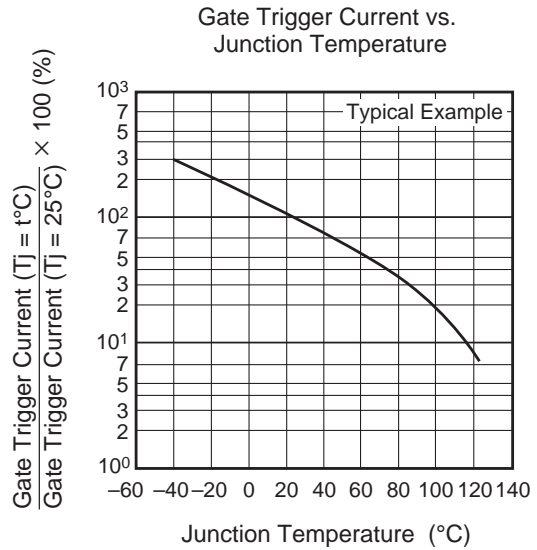
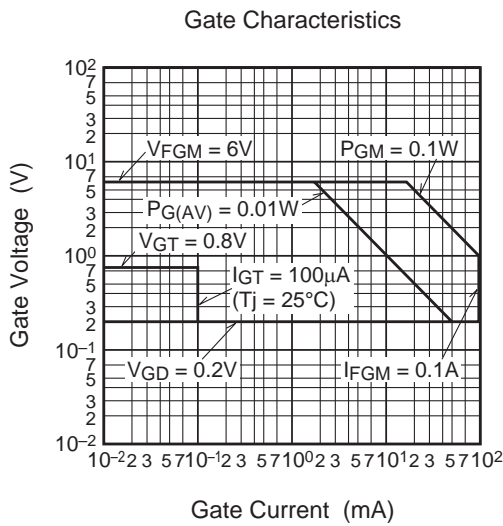
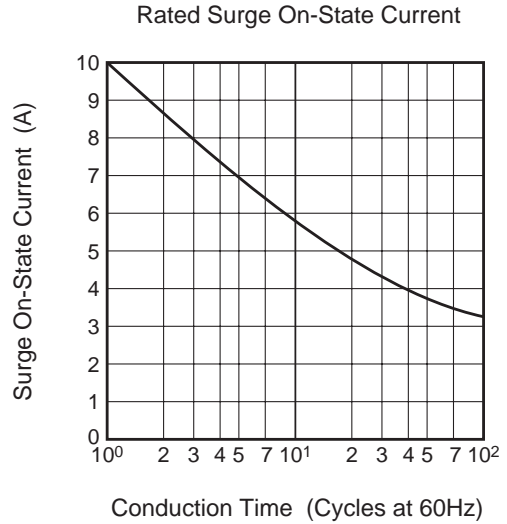
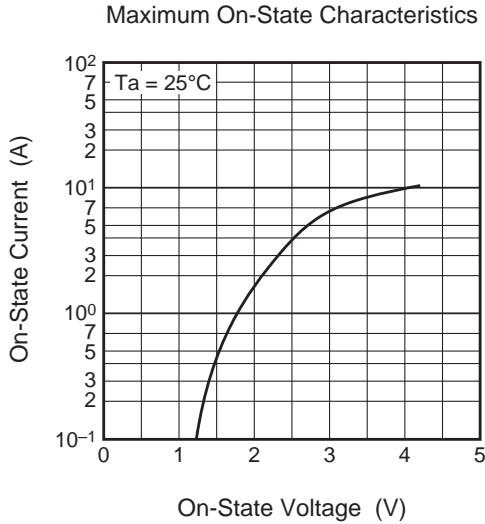
The above values do not include the current flowing through the 1 k Ω resistance between the gate and cathode.

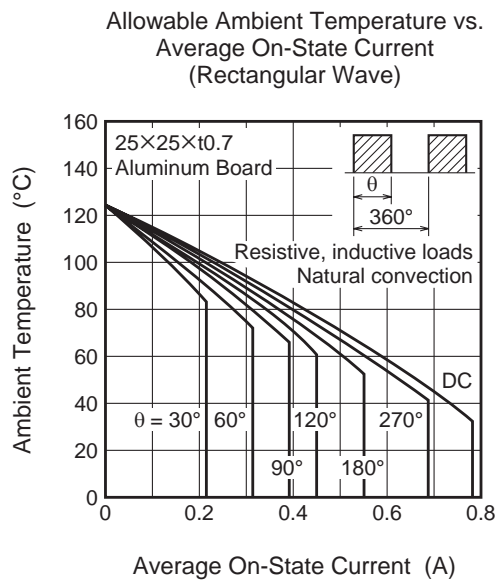
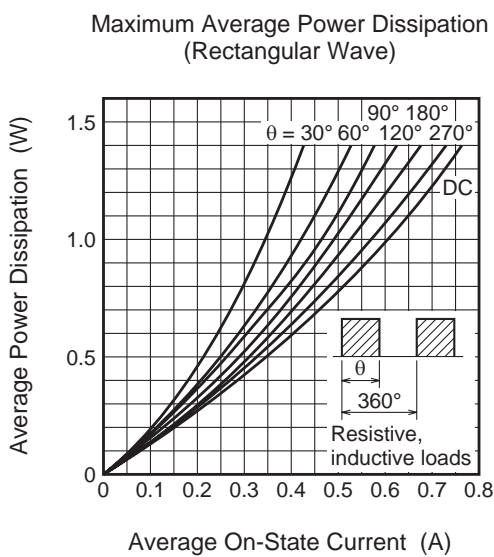
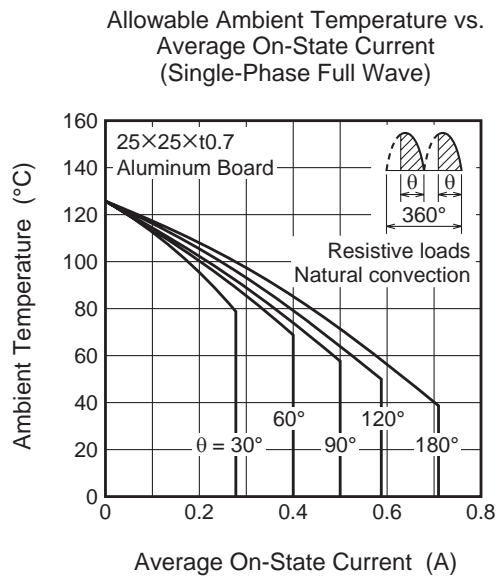
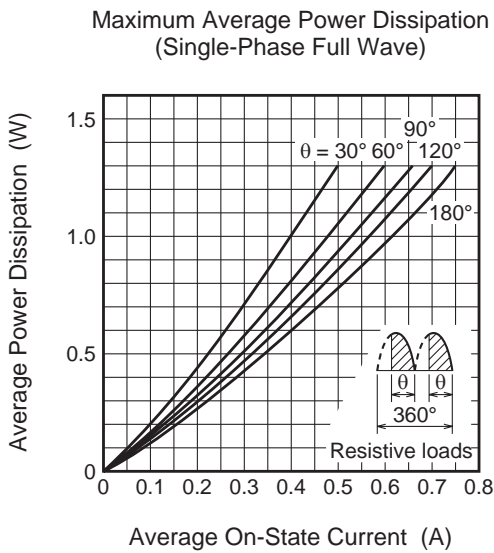
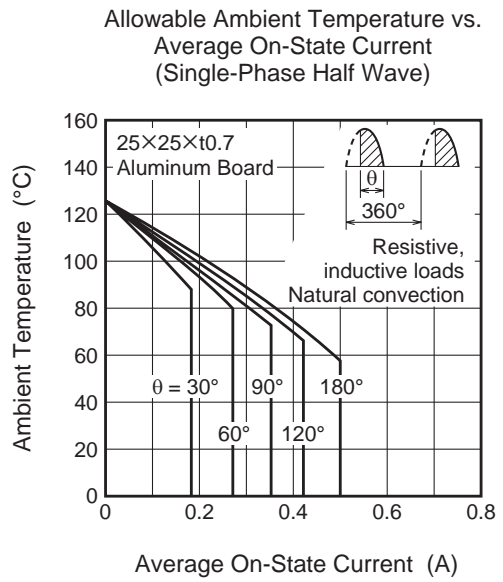
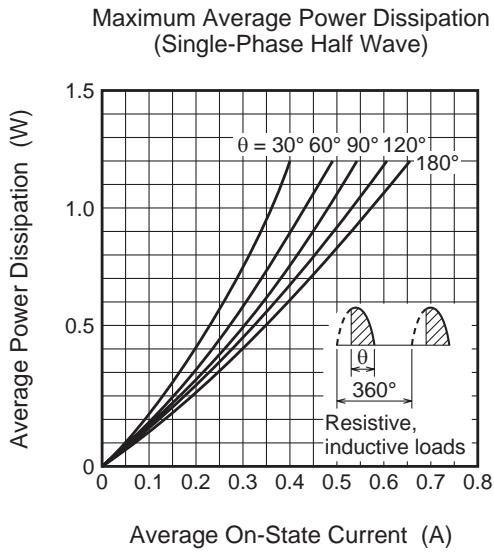
4. I_{GT} , V_{GT} measurement circuit.



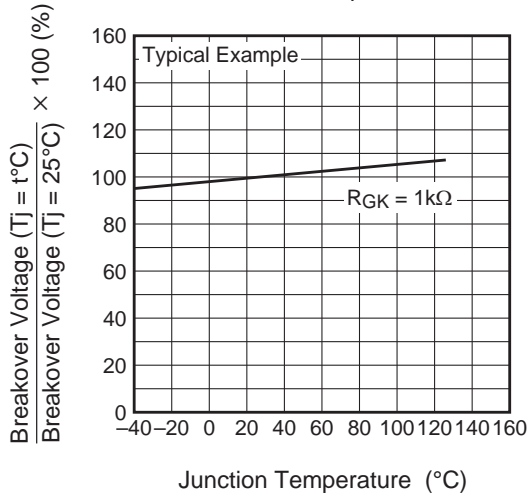
Switch 1 : I_{GT} measurement
 Switch 2 : V_{GT} measurement
 (Inner resistance of voltage meter is about 1k Ω)

Performance Curves

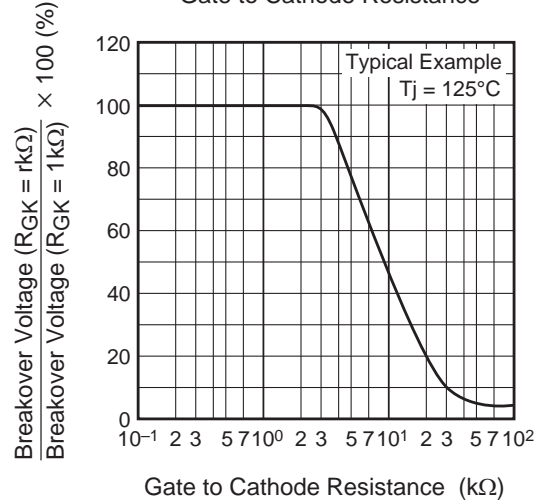




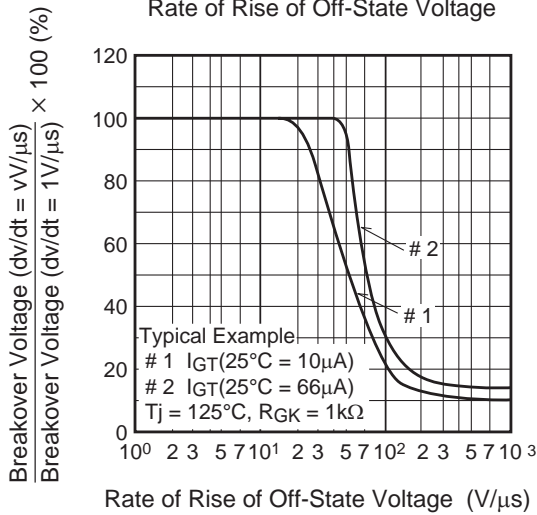
Breakover Voltage vs. Junction Temperature



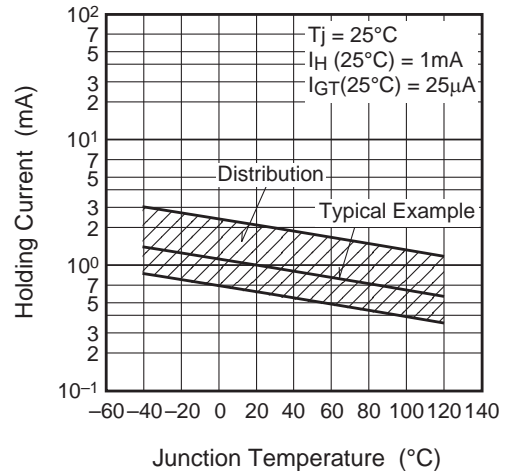
Breakover Voltage vs. Gate to Cathode Resistance



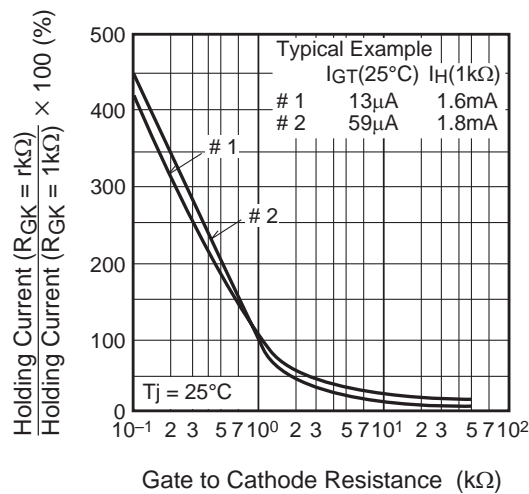
Breakover Voltage vs. Rate of Rise of Off-State Voltage



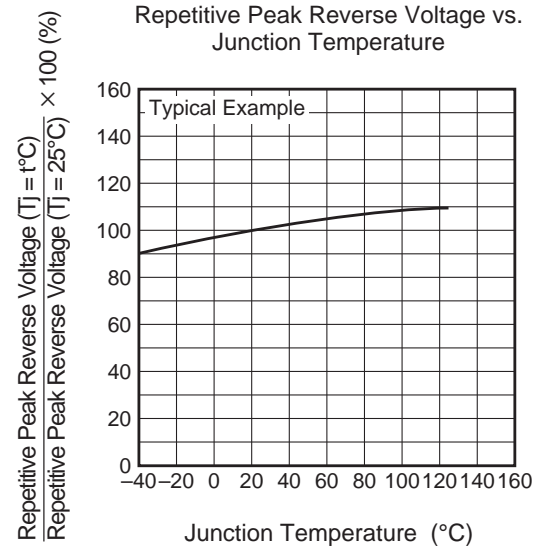
Holding Current vs. Junction Temperature

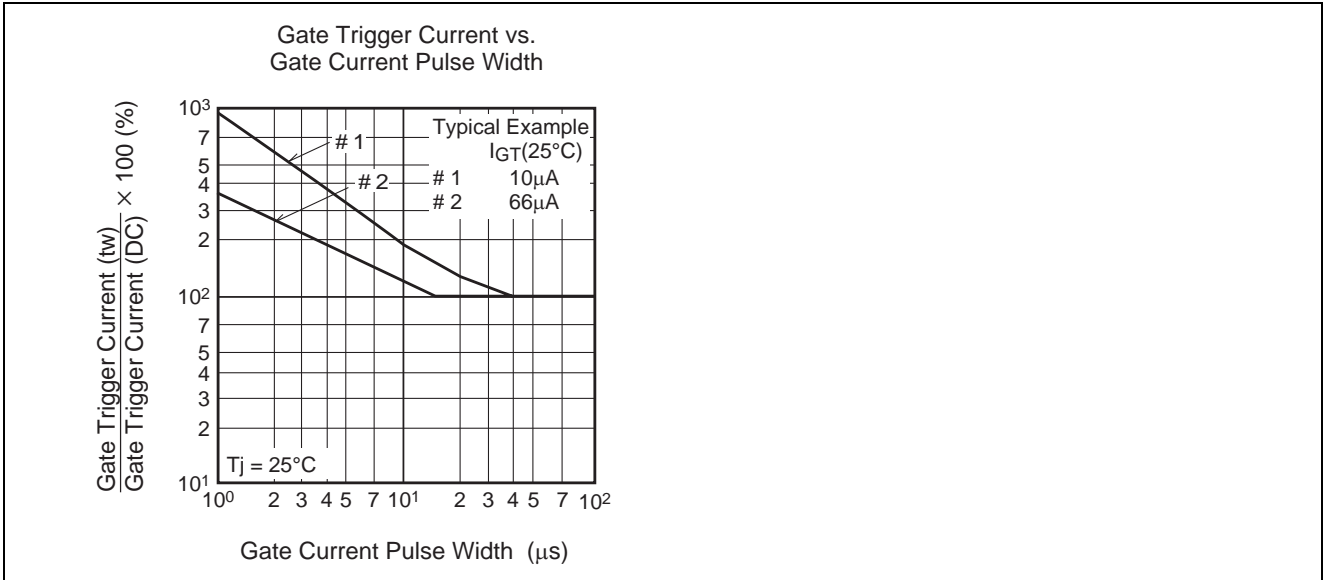


Holding Current vs. Gate to Cathode Resistance

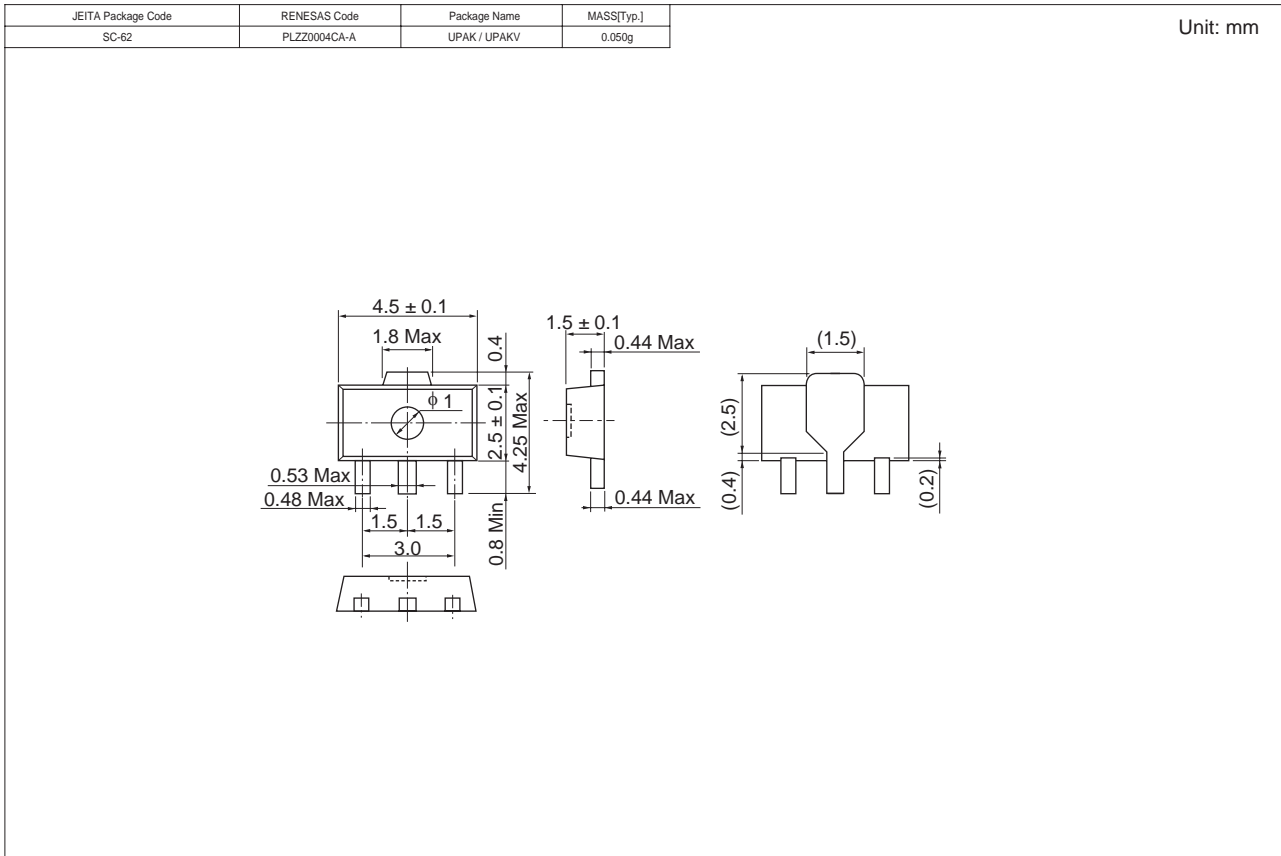


Repetitive Peak Reverse Voltage vs. Junction Temperature





Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	4000	Type name – ET +Direction (1 or 2) + 4	CR05AS-8-ET14

Note : Please confirm the specification about the shipping in detail.

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